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L Number	Hits	Search Text	DB	Time stamp
1	32	5676587.pn. 5853604.uref. 5827781.uref.	USPAT;	2003/07/17 12:02
1	32	3070307.pm. 3033004.uren 3027701.uren	US-PGPUB	2003/07/17 12.02
2	8	5733177.uref.	USPAT;	2003/07/17 12:03
_	J	3733177 (di ci.	US-PGPUB	2000/07/27 12:05
3	11	(((cmp (chemical near mechanical)) with (copper cu	USPAT:	2003/07/17 12:03
Ĭ		conduct\$4 metal))) same (relative near2 (speed velocity))	US-PGPUB	
4	108	((438/626.ccls. 438/633.ccls. 438/687.ccls. 438/690.ccls.	USPAT;	2003/07/17 12:04
-		438/691.ccls. 438/692.ccls. 451/41.ccls.) and (relative	US-PGPUB	
		near2 (speed velocity))) and ((cmp (chemical near		
	i	mechanical)) with (copper cu conduct\$4 metal))		
5	3	((438/626.ccls. 438/633.ccls. 438/687.ccls.) and	USPAT;	2003/07/17 12:05
		(438/690.ccls. 438/691.ccls. 438/692.ccls. 451/41.ccls.))	US-PGPUB	
		and (relative near2 (speed velocity))		
6	17	(((cmp (chemical near mechanical)) with (copper cu	USPAT;	2003/07/17 12:06
		conduct\$4 metal))) same ((relative linear) near2 (speed	US-PGPUB	
		velocity))		2002/07/47 48 67
7	21	(((cmp (chemical near mechanical)) with (copper cu	USPAT;	2003/07/17 12:07
		conduct\$4 metal))) same ((rotat\$6 near2 (speed velocity))	US-PGPUB	
•	_	rpm rpms) same (change decreas\$4 reduc\$5)	EDO: 100:	2002/07/17 12:07
8	3	(((cmp (chemical near mechanical)) with (copper cu	EPO; JPO; DERWENT;	2003/07/17 12:07
		conduct\$4 metal))) and (relative near2 (speed velocity))	IBM TDB	
9	89	(cmp (chemical near mechanical) polish\$4) and ((carrier	USPAT;	2003/07/17 12:08
	0,5	head) same (retain\$4 ring) same membrane same (platen	US-PGPUB	2003/07/17 12:00
		pad) same (pressure psi pa)) and (wafer substrate)	00 1 01 05	
10	125	(438/626.ccls. 438/633.ccls. 438/687.ccls. 438/690.ccls.	USPAT;	2003/07/17 12:08
20		438/691.ccls. 438/692.ccls. 451/41.ccls.) and (((cmp	US-PGPUB	,,
		(chemical near mechanical) polish\$4) with (copper cu		
		conduct\$4 metal)) and ((carrier head) same (retain\$4 ring		
		membrane) same (platen pad) same (pressure psi pa)) and		
		(wafer substrate))		
11	126	((cmp (chemical near mechanical) polish\$4) and ((carrier	EPO; JPO;	2003/07/17 12:09
		head) same (retain\$4 ring membrane)) and (platen pad))	DERWENT;	
		and (pressure psi pa copper cu metal conduct\$4)	IBM_TDB	
12	4	(cmp (chemical near mechanical) polish\$4) and (wafer	USPAT;	2003/07/17 12:09
		substrate) and ((carrier head) same (platen pad) same (rpm	US-PGPUB	
40	_	adj second))	LICDAT	2002/07/47 42:00
13	0	(cmp (chemical near mechanical) polish\$4) and (wafer	USPAT;	2003/07/17 12:09
		substrate) and ((carrier head) same (platen pad) same	US-PGPUB	
14	2	((rpm rotat\$6) near accelerat\$5)) (cmp (chemical near mechanical) polish\$4) and (wafer	USPAT;	2003/07/17 12:10
14		substrate)_and ((carrier head) same (platen pad) same	US-PGPUB	2003/07/17 12:10
		((rpm rotat\$6) with accelerat\$5))	03-10100	1
15	30	((rpm rotats)) with accelerats)) (cmp (chemical near mechanical) polish\$4) and (wafer	USPAT;	2003/07/17 12:10
15	30	substrate) and ((carrier head) same (platen pad) same	US-PGPUB	2303,07,17 12.10
		accelerat\$5)	33 . 3. 35	
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